

In the Specification:

Please delete replacement paragraph [0088] for page 31 of the specification that was submitted on December 12, 2003 and replace it with the new replacement paragraph, marked to show the changes made, set forth below.

Composition concentrations, for one example, are shown in Table 7 and it should be noted that the concentration of, *inter alia*, the Insoluble Complexing Agent of the present invention may be changed to alter the resultant slurry. The concentration of Insoluble Complexing Agent 1,6-dioxaspirol [4,4] nonane 2,7-dione used for etching tests was from about 0.01% to about 0.2 % by weight. As used for CMP, the concentration was from about 0.05% to about 0.1%.

RFST AVAILABLE COPY

Please delete Table 9 on page 37 of the specification, and replace it with the replacement Table 9, marked to show the changes made, set forth below.

Table 9

CMP Mixing Ratios, Processes and Results

Slurry Composition Examples 1 through 5	Cu RR		TaN RR
	CMP Process	CMP Process	CMP Process
	(A)	(B)	(C)
	<u>s/pp/ts/ss</u> <u>s/pp/ts/ss/sf</u>	<u>s/pp/ts/ss</u> <u>s/pp/ts/ss/sf</u>	<u>s/pp/ts/ss</u> <u>s/pp/ts/ss/sf</u>
	5/2/90/90	3/2/75/75	3/2/75/75
1) 60% of Oxidizer E, 20% of Abrasive B, and 20% DI water	7867	4785	195
2) 60% of Oxidizer E, 20% of Abrasive B, 0.5% NH ₂ NH ₂ and 19.5% DI water (pH approximately 3)	4648	2557	182
3) 60% of Oxidizer E, 20% of Abrasive B, 0.25% NH ₂ NH ₂ and 19.75% DI water (pH approximately 3)	6001	3444	193
4) 30% of CMP 9011, 20% of Abrasive B, 0.5% of H ₂ O ₂ 5% Benzotriazole (@ 0.2% solution) and 44.5% DI water	586	183	185
5) 4.8% Hydroxylamine (@ 50% solution), 3.0% Hydroxylamine Sulfate (solid), 5.0% NH ₂ NH ₂ , 4.2% H ₂ SO ₄ , 20% of Abrasive B, and 63.0% DI water	7028	3833	179

BEST AVAILABLE COPY